

Claims

[c1] What is claimed is:

- 1.A method of manufacturing a reflector comprising:
 - providing a substrate;
 - forming at least one thin film transistor on the substrate;
 - forming a plurality of stacked structures on the substrate, each of the stacked structures comprising a plurality of sub-stacked layers, which have at least two different kinds of widths;
 - forming a thin film layer for covering the thin film transistor and the plurality of stacked structures;
 - forming a contact hole in the thin film layer; and
 - depositing a reflective metal layer on the thin film layer;
 - wherein the reflective metal layer is electrically connected to the thin film transistor through the contact hole.

[c2] 2.The method of claim 1 wherein the thin film transistor and the plurality of stacked structures are formed on the substrate simultaneously.

[c3] 3.The method of claim 1 wherein the thin film transistor and the plurality of stacked structures are formed on the substrate asynchronously.

[c4] 4.The method of claim 1 wherein the thin film layer is a laminated layer comprising a photoresist layer, an organic layer, and an inorganic passivation layer.

[c5] 5.The method of claim 4 wherein a method of forming the contact hole comprises:

- forming the inorganic passivation layer on the thin film transistor and the plurality of stacked structures;
- forming the organic layer on the inorganic passivation layer;
- forming the photoresist layer on the organic layer;
- performing a photolithography process for forming a predetermined pattern in the photoresist layer;
- etching the organic layer and the inorganic passivation layer along the predetermined pattern so as to form the contact hole;

removing the photoresist layer; and
performing a baking process for smoothening the organic layer.

[c6] 6.The method of claim 1 wherein the thin film layer is a laminated layer comprising an organic layer and an inorganic passivation layer, and the organic layer is made of a photoresist material.

[c7] 7.The method of claim 6 wherein a method of forming the contact hole comprises:
forming the inorganic passivation layer on the thin film transistor and the plurality of stacked structures;
forming the organic layer on the inorganic passivation layer;
performing a photolithography process for forming a predetermined pattern in the organic layer;
etching the inorganic passivation layer along the predetermined pattern so as to form the contact hole; and
performing a baking process for smoothening the organic layer.

[c8] 8.The method of claim 1 wherein the thin film layer is an organic passivation layer, which is made of a photoresist material.

[c9] 9.The method of claim 8 wherein a method of forming the contact hole comprises:
forming the organic passivation layer on the thin film transistor and the plurality of stacked structures;
performing an exposing process for forming a predetermined pattern in the organic passivation layer;
performing a developing process on the organic passivation layer so as to form the contact hole; and
performing a baking process for smoothening the organic passivation layer.

[c10] 10.The method of claim 1 wherein each of the sub-stacked layers is formed from a material selected from the group consisting of an insulating layer, a gate electrode layer, an amorphous silicon layer, an N⁺ silicon layer, and a metal layer.

[c11] 11. The method of claim 1 wherein each of the sub-stacked layers is formed from a material selected from the group consisting of a gate electrode, a common electrode, an insulating layer, an amorphous silicon layer, an N⁺ silicon layer, a metal layer, a source electrode, a drain electrode, and a passivation layer.